

SKiiP 28AHB16V1



MiniSKiiP[®] 2

3-phase bridge rectifier +
brake chopper

SKiiP 28AHB16V1

Features

- Fast Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications*

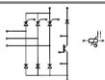
- Input bridge for inverter up to 39 kVA

Remarks

- V_{CEsat} , V_F = chip level value

| Absolute Maximum Ratings | | $T_s = 25^\circ\text{C}$, unless otherwise specified | |
|--------------------------------------|---|---|----------------------|
| Symbol | Conditions | Values | Units |
| IGBT - Chopper | | | |
| V_{CES} | | 1200 | V |
| I_C | $T_s = 25 (70)^\circ\text{C}$ | 118 (88) | A |
| I_{CRM} | $t_p \leq 1 \text{ ms}$ | 210 | A |
| V_{GES} | | ± 20 | V |
| T_J | | -40 ... +150 | $^\circ\text{C}$ |
| Diode - Chopper | | | |
| I_F | $T_s = 25 (70)^\circ\text{C}$ | 118 (88) | A |
| I_{FRM} | $t_p \leq 1 \text{ ms}$ | 210 | A |
| T_J | | -40 ... +150 | $^\circ\text{C}$ |
| Diode / Thyristor - Rectifier | | | |
| V_{RRM} | | 1600 | V |
| I_F / I_T | $T_s = 70$ | 82 | A |
| I_{TSM} / I_{TSM} | $t_p = 10 \text{ ms}$, $\sin 180^\circ$, $T_J = 25^\circ\text{C}$ | 1000 | A |
| P_T | $t_p = 10 \text{ ms}$, $\sin 180^\circ$, $T_J = 25^\circ\text{C}$ | 5500 | A^2s |
| T_J | | -40 ... +150 | $^\circ\text{C}$ |
| T_J | Thyristor | -40 ... +125 | $^\circ\text{C}$ |
| I_{RMS} | per power terminal (20 A / spring) | 120 | A |
| T_{stg} | $T_{op} \leq T_{stg}$ | -40 ... +125 | $^\circ\text{C}$ |
| V_{fwd} | AC, 1 min. | 2500 | V |

| Characteristics | | $T_s = 25^\circ\text{C}$, unless otherwise specified | | | |
|------------------------|--|---|-----------|-----------|---------------|
| Symbol | Conditions | min. | typ. | max. | Units |
| IGBT - Chopper | | | | | |
| V_{CEsat} | $I_{Cnom} = 105 \text{ A}$, $T_J = 25 (125)^\circ\text{C}$ | | 1,7 (2) | 2,1 (2,4) | V |
| $V_{GE(DF)}$ | $V_{GE} = V_{CE}$, $I_C = 3 \text{ mA}$ | 5 | 5,8 | 6,5 | V |
| $V_{CE(TC)}$ | $T_J = 25 (125)^\circ\text{C}$ | | 1 (0,9) | 1,2 (1,1) | V |
| r_T | $T_J = 25 (125)^\circ\text{C}$ | | 6,7 (10) | 8,6 (12) | m Ω |
| C_{ies} | $V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$ | | 8,4 | | nF |
| C_{oes} | $V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$ | | 1,5 | | nF |
| C_{res} | $V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$ | | 1,1 | | nF |
| $R_{th(j-s)}$ | per IGBT | | 0,4 | | K/W |
| $t_{(on)}$ | under following conditions | | 65 | | ns |
| $t_{(off)}$ | $V_{CC} = 600 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$ | | 30 | | ns |
| $t_{(off)}$ | $I_{Cnom} = 105 \text{ A}$, $T_J = 125^\circ\text{C}$ | | 410 | | ns |
| t_f | $R_{coe} = R_{coff} = 5,5 \Omega$ | | 100 | | ns |
| E_{on} | inductive load | | 14,4 | | mJ |
| E_{off} | | | 13,3 | | mJ |
| Diode - Chopper | | | | | |
| $V_F = V_{EC}$ | $I_{Fnom} = 105 \text{ A}$, $T_J = 25 (125)^\circ\text{C}$ | | 1,6 (1,6) | 1,8 (1,8) | V |
| $V_{(TC)}$ | $T_J = 25 (125)^\circ\text{C}$ | | 1 (0,6) | 1,1 (0,9) | V |
| r_T | $T_J = 25 (125)^\circ\text{C}$ | | 5,7 (7,6) | 6,7 (8,6) | m Ω |
| $R_{th(j-s)}$ | per diode | | 0,55 | | K/W |
| I_{FRM} | under following conditions | | 160 | | A |
| O_{rr} | $I_{Fnom} = 105 \text{ A}$, $V_R = 600 \text{ V}$ | | 26 | | μC |
| E_{rr} | $V_{CE} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$ | | 10,8 | | mJ |
| | $di_p/dt = 5400 \text{ A}/\mu\text{s}$ | | | | |



AHB

| Characteristics | | $T_s = 25\text{ }^\circ\text{C}$, unless otherwise specified | | | |
|------------------------------|--|---|------------|-----------|------------------|
| Symbol | Conditions | min. | typ. | max. | Units |
| Diode - Rectifier | | | | | |
| V_F | $I_{F\text{nom}} = 75\text{ A}$, $T_J = 25\text{ }^\circ\text{C}$ | | 1.2 | | V |
| $V_{T(TC)}$ | $T_J = 150\text{ }^\circ\text{C}$ | | 0.8 | | V |
| r_T | $T_J = 150\text{ }^\circ\text{C}$ | | 7 | | m Ω |
| $R_{th(j-s)}$ | per diode | | 0.7 | | K/W |
| Thyristor - Rectifier | | | | | |
| V_T | $I_{T\text{nom}} = 120\text{ A}$, $T_J = 25\text{ (125)}\text{ }^\circ\text{C}$ | | | 1.8 (1.7) | V |
| $V_{T(TC)}$ | $T_J = 125\text{ }^\circ\text{C}$ | | | 1.1 | V |
| r_T | $T_J = 125\text{ }^\circ\text{C}$ | | | 5 | m Ω |
| V_{GT} | $T_J = 25\text{ }^\circ\text{C}$ | | | 3 | V |
| I_{GT} | $T_J = 25\text{ }^\circ\text{C}$ | 150 | | | mA |
| I_H | $T_J = 25\text{ }^\circ\text{C}$ | | 200 | | mA |
| I_L | $T_J = 25\text{ }^\circ\text{C}$ | | 400 | | mA |
| $dv/dt_{(cr)}$ | $T_J = 125\text{ }^\circ\text{C}$ | | | 1000 | V/ μs |
| $di/dt_{(cr)}$ | $T_J = 125\text{ }^\circ\text{C}$ | | | 50 | A/ μs |
| $R_{th(j-s)}$ | per thyristor | | 0.65 | | K/W |
| Temperature Sensor | | | | | |
| R_{ts} | 3 %, $T_r = 25\text{ (100)}\text{ }^\circ\text{C}$ | | 1000(1670) | | Ω |
| Mechanical Data | | | | | |
| w | | | 65 | | g |
| M_b | Mounting torque | 2 | | 2.5 | Nm |

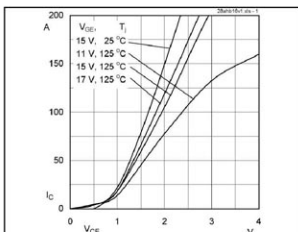


Fig. 1 Typ. output characteristic

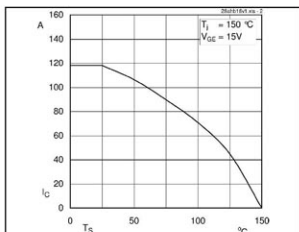


Fig. 2 Typ. rated current vs. temperature

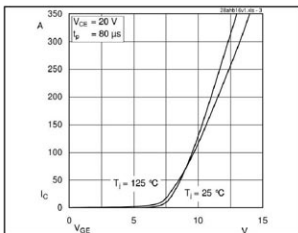


Fig. 3 Typ. transfer characteristic

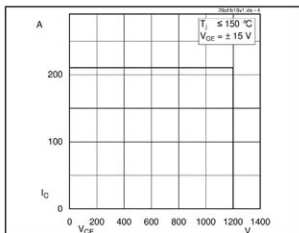


Fig. 4 Reverse bias safe operating area

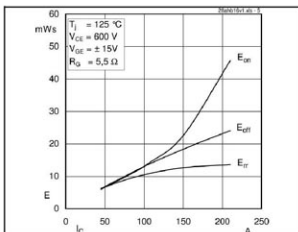


Fig. 5 Typ. Turn-on / off energy = $f(I_C)$

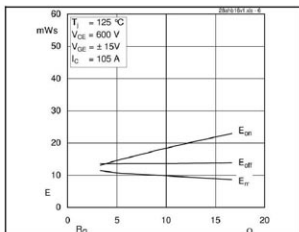


Fig. 6 Typ. Turn-on / off energy = $f(R_G)$

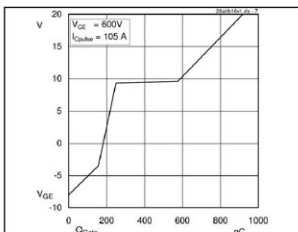


Fig. 7 Typ. gate charge characteristic

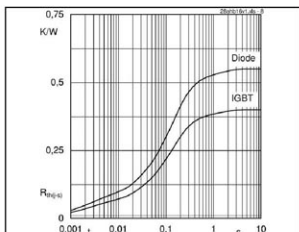


Fig. 8 Typ. thermal impedance

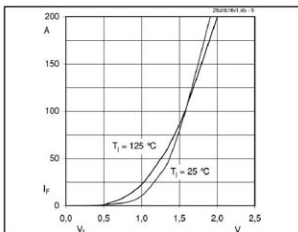


Fig. 9 Typ. freewheeling diode forward characteristic

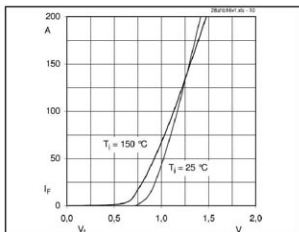


Fig. 10 Typ. input bridge forward characteristic

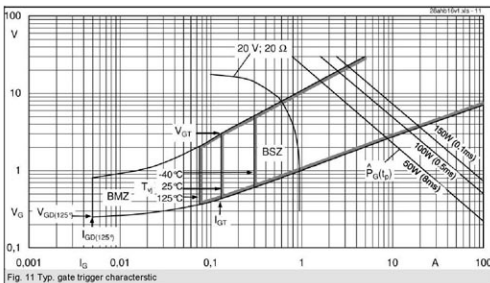


Fig. 11 Typ. gate trigger characteristic

